

**Silicon NPN transistor epitaxial type
6C955**
[Applications]

General purpose amplifier

[Feature]

 Low saturation voltage $V_{CE(sat)} = 0.5V$ (Max.) at $I_C = 500mA$, $I_B = 50mA$
 PNP complementary pair with A5955

[Absolute maximum ratings (Ta=25C)]

Characteristic	Symbol	Maximum ratings	Unit
Collector-base voltage	VCBO	120	V
Collector-emitter voltage	VCEO	100	V
Emitter-base voltage	VEBO	6	V
Collector current	IC	1	A
Junction temperature	Tj	150	C
Storage temperature	Tstg	-55 to 150	C

[Electrical characteristics (Ta=25C)]

Characteristic	Symbol	Min.	Typ.	Max.	Unit	Conditions
Collector-base breakdown voltage	BVCBO	120	-	-	V	IC= 100uA
Collector-emitter breakdown voltage	BVCEO	100	-	-	V	IC= 10mA
Emitter-base breakdown voltage	BVEBO	6	-	-	V	IE= 100uA
Collector cut-off current	ICBO	-	-	500	nA	VCB= 120V
Emitter cut-off current	IEBO	-	-	500	nA	VEB= 6V
DC current gain 1	hFE 1	140	220	330	-	VCE= 2V, IC= 150mA
DC current gain 2	hFE 2	40	-	-	-	VCE= 5V, IC= 1A
Collector-emitter saturation voltage	VCE(sat)	-	-	0.5	V	IC= 500mA, IB= 50mA
Base-emitter saturation voltage	VBE(sat)	-	-	1.1	V	IC= 500mA, IB= 50mA
Transition frequency	fT	100	-	-	MHz	VCE= 5V, IE= -50mA
Collector output capacitance	Cob	-	-	10	pF	VCB= 10V, f = 1MHz, IE= 0A

Notice 1) These are measured data of transistors assembled by PHENITEC SEMICONDUCTOR Corp. and are for reference only.

Notice 2) The contents described herein are subject to change without notice.

